WHAT IS CLAIMED IS:

1. A manufacturing method for a device chip, comprising:

a wafer preparation step of preparing a wafer including a base substrate, a laser beam absorbing layer layered on a front surface of the base substrate, and a device layer being layered on the laser beam absorbing layer and having devices formed in respective separate regions demarcated by a plurality of crossing division lines;

a device layer dividing step of forming respective division grooves that divide at least the device layer into individual device chips along the plurality of division lines; and

a lift-off step of, after the device layer dividing step is carried out, applying a laser beam of such a wavelength as to be absorbed in the laser beam absorbing layer, from the base substrate side, and lifting off a device chip from the front surface of the base substrate,

wherein, in the lift-off step, a focusing point of the laser beam is moved onto a trajectory in a spiral shape from an outermost peripheral edge of the laser beam absorbing layer in a circumferential direction thereof toward a center of the laser beam absorbing layer.

2. The manufacturing method for a device chip according to claim 1, further comprising:

a transfer member arranging step of arranging a transfer member to a front surface of the device layer, before the lift-off step is carried out.

3. The manufacturing method for a device chip according to claim 2, wherein the transfer member is attached to an adhesive and arranged to the front surface of the device layer through the adhesive, and the adhesive reduces its adhesion force as a result of application of ultraviolet light or heating.